

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	16	kirkpatrick near brian.in.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:36	
2	BRS	L2	1	montgomery near clint.in.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:36	
3	BRS	L3	3	trentman near brian.in.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:36	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	1539	438/706.ccls.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:37	
5	BRS	L5	518	4 and (plasma near etch\$3)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:37	
6	BRS	L6	6	4 and (plasma near etch\$3) near15 (hardmask or hard- mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:41	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	103	(plasma near etch\$3) near15 (hardmask or hard- mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:42	
8	BRS	L8	0	(plasma near etch\$3) near15 (hardmask or hard- mask) near15 (modified)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:42	
9	BRS	L9	1	(plasma near etch\$3) near15 (hardmask or hard- mask) same (modified)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:43	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	1	(etch\$3) near15 (hardmask or hard-mask) near25 (modified)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:43	
11	BRS	L12	0	(etch\$3) near15 (hardmask or hard-mask or hard near mask) near25 (modified near layer)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:44	
12	BRS	L11	14	(etch\$3) near15 (hardmask or hard-mask or hard near mask) near25 (modified)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:07	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	49	(etch\$3) near15 (hardmask or hard- mask or hard near mask) near25 (clean)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 16:00	
14	BRS	L14	2400	(etch\$3) near15 (hardmask or hard- mask or hard near mask) near25 (remov\$3)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 16:19	
15	BRS	L16	1	(plasma near5 etch\$3) near15 (hardmask or hard- mask or hard near mask) near25 (remov\$3) near25 (clean)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 16:20	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L15	212	(plasma near5 etch\$3) near15 (hardmask or hard- mask or hard near mask) near25 (remov\$3)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 16:45	
17	BRS	L17	4	(plasma near5 etch\$3) near15 (hardmask or hard- mask or hard near mask) near25 (transistor\$1)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 16:46	
18	BRS	L18	113	(etch\$3) near15 (hardmask or hard- mask or hard near mask) near25 (transistor\$1)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 16:52	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
19	BRS	L19	0	(etch\$3) near15 (hardmask or hardmask or hard near mask) near25 (transistor\$1) near15 (interconnect\$1 or inter-connect\$1)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/29 16:53	
20	BRS	L20	0	(etch\$3) near15 (hardmask or hardmask or hard near mask) near25 (transistor\$1) near35 (interconnect\$1 or inter-connect\$1)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/29 16:53	
21	BRS	L21	18	(etch\$3) near15 (hardmask or hardmask or hard near mask) near25 (transistor\$1) near35 (opening\$1 or trench\$3)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/29 16:54	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
22	BRS	L22	234	(isotropic) near15 (phosphoric near acid)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:08	
23	BRS	L23	214	(isotropic near3 etch\$3) near15 (phosphoric near acid)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:08	
24	BRS	L24	0	(isotropic near3 etch\$3) near15 (phosphoric near acid) near15 (hardmask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:09	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
25	BRS	L25	0	(isotropic near3 etch\$3) near15 (phosphoric near acid) near15 (hard- mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:09	
26	BRS	L26	7	(isotropic near3 etch\$3) near15 (phosphoric near acid) near15 (hard near mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:13	
27	BRS	L27	7	(isotropic near3 etch\$3) near15 (phosphoric) near15 (hard near mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:13	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
28	BRS	L28	4	(isotropic near etch\$3) near15 (phosphoric) near15 (hard near mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:14	
29	BRS	L29	2	(remov\$3) near25 (isotropic near etch\$3) near15 (phosphoric) near15 (hard near mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:16	
30	BRS	L30	43	(remov\$3) near25 (isotropic near etch\$3) near15 (hard near mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:17	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
31	BRS	L31	2	(remov\$3) near15 (plasma) near25 (isotropic near etch\$3) near15 (hard near mask)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 17:17	

	U	1	PT	P	Document ID	Issue Date	Page s	Title
1					US 2004022945 2 A1	20041118	6	Densifying a relatively porous material
2					US 2003012774 0 A1	20030710	10	Air gaps copper interconnect structure
3					US 2003006457 7 A1	20030403	10	METHOD OF MAKING AIR GAPS COPPER INTERCONNECT
4					US 2003004777 7 A1	20030313	12	Edge termination in a trench-gate MOSFET
5					US 2002000673 0 A1	20020117	14	Fine pattern formation method and semiconductor device or liquid crystal device manufacturing method employing this method

	U	1	PT	P	Document ID	Issue Date	Page s	Title
6					US 2001002695 6 A1	20011004	8	Fluorinated hard mask for micropatterning of polymers
7					US 6762064 B1	20040713	10	Process for fabrication of a ferrocapacitor
8					US 6614094 B2	20030902	12	High integration density vertical capacitor structure and fabrication process
9					US 6589880 B2	20030708	13	Fine pattern formation method and semiconductor device or liquid crystal device manufacturing method employing this method
10					US 6555467 B2	20030429	8	Method of making air gaps copper interconnect

	U	1	PT	P	Document ID	Issue Date	Page s	Title
11					US 6492222 B1	20021210	19	Method of dry etching PZT capacitor stack to form high-density ferroelectric memory devices
12					US 6287961 B1	20010911	19	Dual damascene patterned conductor layer formation method without etch stop layer
13					US 6245489 B1	20010612	8	Fluorinated hard mask for micropatterning of polymers
14					EP 911697 A2	19990428	ERR	A fluorinated hard mask for micropatterning of polymers